

Jie Chen

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Investigations on Averaging Mechanisms of Virtual Junction Temperature Determined by $V_{CE}(T)$ Method for IGBTs. IEEE Transactions on Electron Devices, 2020, 67, 1106-1112.	3.0	25
2	Sequential $V_{CE}(T)$ Method for the Accurate Measurement of Junction Temperature Distribution Within Press-Pack IGBTs. IEEE Transactions on Power Electronics, 2021, 36, 3735-3743.	7.9	17
3	Study of IGBTs Reliability Under Coupled Electrical"Thermal Environment. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 4260-4268.	5.4	10
4	Junction-to-Case Thermal Resistance Measurement and Analysis of Press-Pack IGBTs Under Double-Side Cooling Condition. IEEE Transactions on Power Electronics, 2022, 37, 8543-8553.	7.9	10
5	Influence of the clamping force on the power cycling lifetime reliability of press pack IGBT sub–module. Journal of Engineering, 2019, 2019, 2435-2439.	1.1	9
6	The Distributed Heat Source Modeling Method for the Finite Element Simulation of IGBTs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2021, 11, 83-89.	2.5	5
7	The Influence and Application of Bond Wires Failure on Electrothermal Characteristics of IGBT Module. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2021, 11, 1426-1434.	2.5	5
8	Temperature Distribution Evaluation of Single Chip by Multiple Currents $V_{CE}(T)$ Method. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2021, 11, 426-434.	2.5	3
9	Calibration Method of Junction Temperature Measurement for Press-Pack IGBTs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2021, 11, 1063-1072.	2.5	1
10	Investigation on the accuracy of the junction temperature determined by the VCE(T) method under different load pulse durations in power cycling test. Microelectronics Reliability, 2021, 127, 114420.	1.7	0